

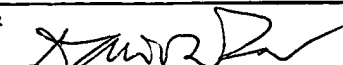
PTO-1449 REPRODUCED SUPPLEMENTAL INFORMATION DISCLOSURE CITATION IN AN APPLICATION November 4, 2004 (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.2033-002		APPLICATION NO. 10/608,780	
	FIRST NAMED INVENTOR Jagdish Narayan		FILING DATE June 27, 2003	
	EXAMINER Nhu, David		CONFIRMATION NO. 8117	GROUP 2818

U.S. PATENT DOCUMENTS				
EXAM- INER INI- TIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT
DN	AC8	6,495,862 B1	12-17-2002	Okazaki <i>et al.</i>
	AD8	US 2001/0032976 A1	10-25-2001	Ishikawa <i>et al.</i>
	AE8	US 2002/0001864 A1	01-03-2002	Ishikawa <i>et al.</i>
	AF8	US 2002/0182765 A1	12-05-2002	Tran <i>et al.</i>
	AG8	6,403,987 B1	06-11-2002	Miki <i>et al.</i>
	AH8	US2002/0047128 A1	04-25-2002	Song <i>et al.</i>
	AI8	6,344,665 B1	02-05-2002	Sung <i>et al.</i>
	AJ8	6,417,525 B1	07-09-2002	Hata
	AK8	5,760,423	06-02-1998	Kamakura <i>et al.</i>
	AA9	6,268,618 B1	07-31-2001	Miki <i>et al.</i>
	AB9	5,656,832	08-12-1997	Ohba <i>et al.</i>
	AC9	5,834,331	11-10-1998	Razeghi
	AD9	5,900,650	05-04-1999	Nitta
	AE9	6,153,894	11-28-2000	Udagawa
	AF9	6,118,801	09-12-2000	Ishikawa <i>et al.</i>
	AG9	6,521,999 B1	02-18-2003	Uemura <i>et al.</i>
	AH9	5,877,558	03-02-1999	Nakamura <i>et al.</i>
	AI9	5,455,195	10-03-1995	Ramsey <i>et al.</i>
	AJ9	6,531,383 B1	03-11-2003	Lee
	AK9	6,445,127 B1	09/03/2002	Oku, <i>et al.</i>
	AA10	6,410,942 B1	06-25-2002	Thibeault, <i>et al.</i>
	AB10	5,726,462	03-10-1998	Spahn, <i>et al.</i>
	AC10	6,060,335	05-09-2000	Rennie, <i>et al.</i>
	AD10	6,287,947 B1	09-11-2001	Ludowise, <i>et al.</i>
	AE10	5,442,205	08-15-1995	Brasen, <i>et al.</i>
DN	AF10	5,637,530	06-10-1997	Gaines, <i>et al.</i>

EXAMINER	DATE CONSIDERED
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
AV6		Chichibu, S., <i>et al.</i> , "Exciton Localization in InGaN Quantum Well Devices," <i>J. Vac. Sci. Technol B.</i> , Vol. 16(4):2204-2214 (1998).
AW6		Chen, L., <i>et al.</i> , "Fabrication of 50-100 nm Patterned InGaN Blue Light Emitting Heterostructures," <i>IEEE, 14th Annual Meeting of the IEEE Lasers & Electro-Optics Society</i> , 1:760-761 (2001).
AX6		Cho, H. K., <i>et al.</i> , "Influence of Strain-Induced Indium Clustering on Characteristics of InGaN/GaN Multiple Quantum Wells with High Indium Composition," <i>Journal of Applied Physics</i> , 91(3):1104-1107 (2002).
AY6		Narayan, J. and H. Wang, "Effect of Thickness Variation in High-Efficiency InGaN/GaN Light-Emitting Diodes," <i>Applied Physics Letters</i> , 81(5): 841-843 (2002).
AZ6		Kim, H., <i>et al.</i> , "Design and Fabrication of Highly Efficient GaN-Based Light-Emitting Diodes," <i>IEEE Transactions on Electron Devices</i> , 49(10):1715-1722 (2002).
AR7		Maeda, T., <i>et al.</i> , "Effects of NiO on Electrical Properties of NiAu-Based Ohmic Contacts for <i>p</i> -type GaN," <i>Applied Physics Letters</i> 75(26):4145-4147 (1999).

EXAMINER 	DATE CONSIDERED 11/24/04
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